



Technical Data	
Pressure	1x10 ⁻³ Pa (1*10 ⁻⁵ mbar), in process 1*10 ⁻² Pa (1*10 ⁻⁴ mbar)
Exhaust System	load lock chamber: dry pump ; main chamber: 1-2 turbo molecular pumps (1800 – 3600 l/s for Ar)
Throughput	< 5 min / wafer 4" inch wafer for < 150 nm material removal
Loading Capacity	double load lock with 2 carriers each carrying 2 x 12", 3 x 8", 4 x 6" or 8 x 4" face-down wafers; optional feed via robot handling
Ion Source	RF type, RF40 or RF80 with a removal rate of up to 0.15 and 0.6 mm ³ /min respectively
Processible Materials	LiNbO ₃ , LiTaO ₃ , SiO ₂ , Si, and others
Prospected Processing Accuracy	sigma < 0,1nm
Footprint*	W3600 x D1700 x H1900 (doors closed)
Weight*	4900 kg

Additional Features	
Diaphragm Changer	automatic ion source spot adjustment with different apertures
ISERM (in-situ etch rate monitoring)	Etch rate determination with accuracy +/- 0,1nm/s
OTFP (Optical Thin Film Probing)	Integrated metrology system via dielectric thin film thickness determination

*final configuration dependant